onsemi

Bipolar Transistor

50 V, 15 A, Low V_{CE(sat)}, NPN TO-220F-3SG

2SC6082

Features

- Adoption of MBIT Process
- Low Collector-to-Emitter Saturation Voltage
- Large Current Capacitance
- High-Speed Switching
- This is a Pb–Free Device

Applications

• High-Speed Switching Applications (Switching Regulator, Driver Circuit)

Specifications

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

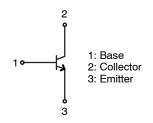
Symbol	Rating	Condition	Value	Unit
V _{CBO}	Collector-to-Base Voltage		60	V
V _{CES}	Collector-to-Emitter Voltage		60	V
V _{CEO}			50	V
V _{EBO}	Emitter-to-Base Voltage		6	V
Ι _C	Collector Current		15	А
I _{CP}	Collector Current (Pulse)	$\begin{array}{l} PW \leq 10 \ \mu s, \\ duty \ cycle \leq 1\% \end{array}$	20	A
Ι _Β	Base Current		3	А
P _C	Collector Dissipation		2	mW
		$T_C = 25^{\circ}C$	23	mW
Tj	Junction Temperature		150	°C
Tstg	Storage Temperature		–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

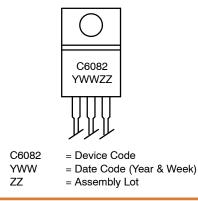


TO-220 Fullpack, 3-Lead / TO-220F-3SG CASE 221AT

ELECTRICAL CONNECTION



MARKING DIAGRAM



ORDERING INFORMATION

Package	Shipping
TO-220F (Pb-Free)	50 / Tube
	<u> </u>

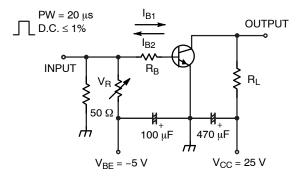
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	Collector Cutoff Current	V _{CB} = 40 V, I _E = 0 A	-	-	10	μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4 \text{ V}, I_{C} = 0 \text{ A}$	-	-	10	μA
H _{FE} 1	DC Current Gain	V_{CE} = 2 V, I_{C} = 330 mA	200	-	560	
H _{FE} 2		V _{CE} = 2 V, I _C = 10 A	50	-	-	
f _T	Gain-Bandwidth Product	V _{CE} = 10 V, I _C = 2 A	-	195	-	MHz
Cob	Output Capacitance	V _{CB} = 10 V, f = 1 MHz	-	85	-	pF
V _{CE} (sat)	Collector-to-Emitter Saturation Voltage	l _C = 7.5 mA, l _B = 375 mA	-	200	400	mV
V _{BE} (sat)	Base-to-Emitter Saturation Voltage	l _C = 7.5 mA, l _B = 375 mA	-	-	1.2	V
V _{(BR)CBO}	Collector-to-Base Breakdown Voltage	I _C = 100 μA, I _E = 0 A	60	-	-	V
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	I_C = 100 μA, R_{BE} = 0 Ω	60	-	-	V
V _{(BR)CEO}		I_{C} = 1 mA, R_{BE} = ∞	50	-	-	V
V _{(BR)EBO}	Emitter-to-Base Breakdown Voltage	I _E = 100 μA, I _C = 0 A	5	-	-	V
t _{on}	Turn-On Time	See specified Test Circuit		52	-	ns
t _{stg}	Storage Time	1		560	-	ns
t _f	Fall Time	1		37	-	ns

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit

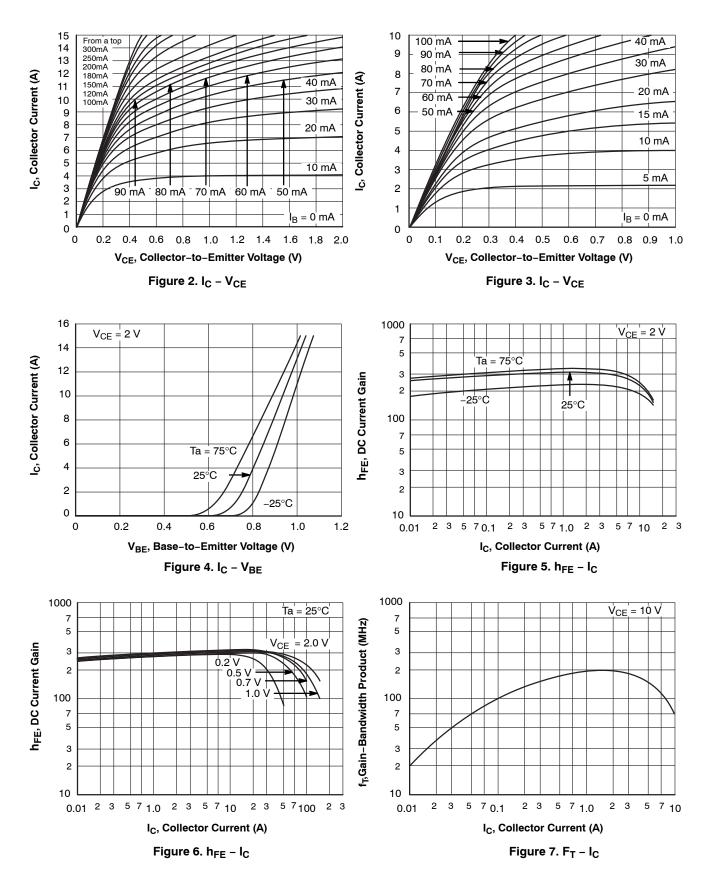


 $I_{\rm C} = 20I_{\rm B1} = -20I_{\rm B2} = 5$ A

Figure 1. Switching Time Test Circuit

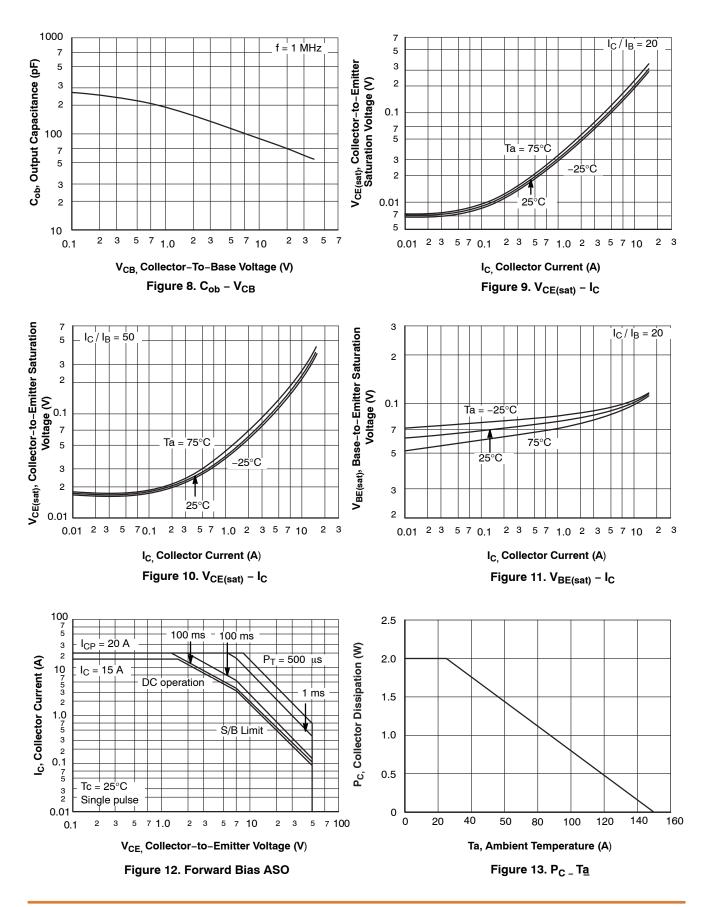
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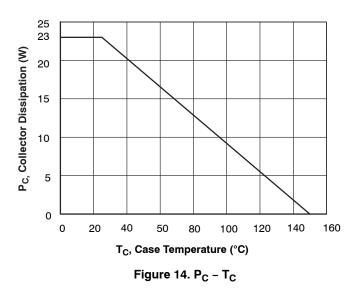
TYPICAL CHARACTERISTICS



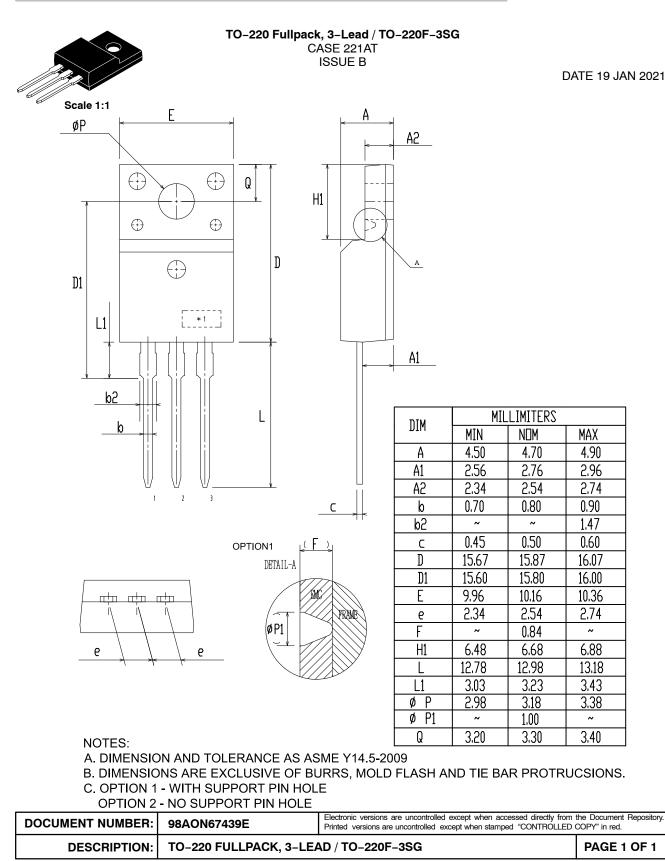
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TYPICAL CHARACTERISTICS (continued)









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